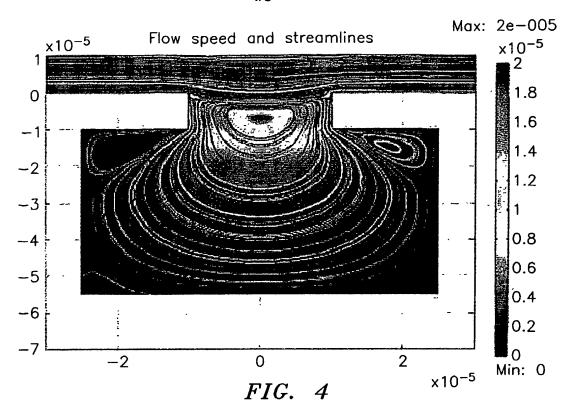
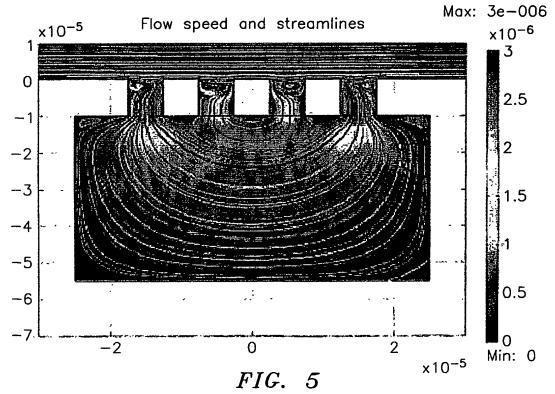


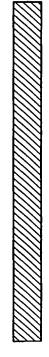
WO 2006/025858 PCT/US2005/005000

4/5

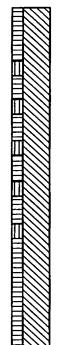




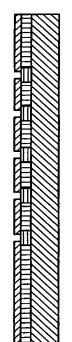
Fabrication of trench geometry



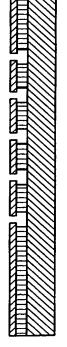
1) Start with a clean glass slide.



2) Spin thick photoresist and expose the confinement channel geometry under a mask aligner. No resist development yet.



3) Deposit a thin layer of silicon nitride or a resist with a very short exposure time.

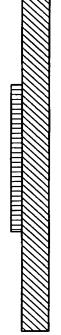


4) Develop the underlying to pattern the trenches.

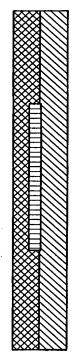
Fabrication of the PDMS channel



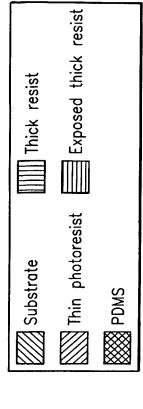
1) Start with a clean silicon substrate.



 Spin thick photoresist and pattern the main flow channel geometry. Treat surfaces with HDMS (to prevent stiction of PDMS).



3) Pour, cure and remove PDMS to micro-mold the main flow channel pattern.



FIC. 6